# EECS 242: Linearization Efficiency Enhancement and Power Combiners

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# Linearization

#### **Polar Modulators**



- Polar modulators are gaining popularity by require complex feedback and/or chip to external PA interaction
- Modulation bandwidth is a limiting factor
- In a digital system, the magnitude/phase signal are generated directly and fed into an offset PLL and PA supply voltage

# **Feedback Loops with PA**

- Need loop gain, stability a big concern, modulation bandwidth
- Envelope feedback only works for AM-AM nonlinearity
- Cartesian requires linear mixers and good amplitude/ phase matching
- Complexity...





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# **Digital Predistortion**



- In a modern system a dynamic predistortion circuit can compensate for process/ temp variations
- Can implement predistortion at baseband
- 100k gates = 1 pad

#### **Microwave Feedforward**



- Basestations use feedforward linearization since calibariton is a possibility.
- Use couplers

### **Dynamic PA**



- Envelope tracking supply and dynamic class-A
- Efficiency always close to peak efficiency of amplifier (say 30%) regardless of PAR
- Need a very fast DC-DC converter

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# How Big?

- The amount of power that we can extract from a PA device is limited by the output imepdance of the device. As the device is made larger to handle a higher DC current (without compromising the  $f_T$ ), the lower the output impedance.
  - For a "current source" style of PA, eventually the device is so large that power is lost in the device rather than the load. This is the attraction of a switching PA.

#### **Gain vs. Output Power Tradeoff**



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#### **Power Devices (cont)**



	Finger width	MSG	Idc
1	1µm	7.6dB	25mA
	2µm	8.4dB	47mA
	4µm	6.8dB	94mA





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# **Power Combining (cont)**

- But for a non-switching PA we must perform some power
   combining to use more than one device. This way we can
   transform the load into a higher
   impedance seen by each PA.
- The power combining networks are lossy and large. We'll come back to them later.



#### **Can we "wire" PAs together?**

Note that we cannot simply "wire" PAs together since the impedance seen by each PA increases by N if we connect N in parallel:

$$R_{PA} = \frac{V_L}{I_L/N} = NR_L$$

This means that each PA delivers less power for a fixed swing

$$P_{PA} = \frac{V_{swing}^2}{2R_{PA}}$$

 There is also "load pulling" effects if the sub-PAs are not perfectly in phase

# **Outphasing LINC Amplifier**



- Decompose the AM/PM signal into two PM signals
- The two PM signals can get amplified by two non-linear PA's. These can be saturated and efficient amplifiers.
- By combining the two signals, the amplitude modulation is restored at the antenna.
- How to combine signals? Simple current mode will present a timevarying load to each PA. Coupler or isolator will waste power.

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# **Outphasing Math**

$$\cos(A) + \cos(B) = 2\cos\left(\frac{A+B}{2}\right)\cos\left(\frac{A-B}{2}\right)$$
$$\cos(\omega t + \phi) + \cos(\omega t - \phi) = 2\cos(\phi)\cos(\omega t)$$
$$\cos(\omega t + \cos^{-1}A(t)) + \cos(\omega t - \cos^{-1}A(t)) = 2\cos(\cos^{-1}A(t))\cos(\omega t)$$
$$\cos(\omega t + \cos^{-1}A(t)) + \cos(\omega t - \cos^{-1}A(t)) = 2A(t)\cos(\omega t)$$

- In theory all we need to do is to compute the inverse cosine of the AM waveform to generate our outphasing signals
- In practice, we can use a DSP to calculate these signals since the envelope rate is at the modulation rate and digital techniques work well
- Power combining is the main difficulty. *UC Berkeley, EECS 242*

# **Doherty Amplifier Concept**



Must efficiently combine power without increasing  $V_{swing}_{\textit{Copyright} © \textit{Prof. Niknejad}}$  16

# **Doherty Amplifier Block Diagram**



Quarter wave line used as an impedance inverter. Can be realized with LC equivalent.

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# **Doherty Details**





- Small signal region: auxiliary amplifier is off
- When the input crosses the threshold, the action of the auxiliary  $Z_{1} = \frac{Z_{T}^{2}}{R_{L}(1 + \frac{I_{2}}{I_{1T}})}$  amplifier is to dynamically lower the load seen by the main load seen by the main PA
  - Finally, both amplifiers operate at the peak

# **Doherty Amplifier Operation**



Auxiliary amplifier actively changes load impedance of the main amplifier

#### **Lumped Doherty Implementation**

- Can use lumped elements to realize 90° phase shift
- The CLC line is an impedance inverter that also provides VDD for the aux amp
- The LCL line is embedded into the matching network and provides 90° phase shift
- Simulations show an improved efficiency

Zhao, M. Iwamoto, D. Kimball, L. Larson, P. Asbeck

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#### **LC Matching Networks**

- Matching networks are needed to drive output power to the load, which has a fixed impedance.
  - Large output powers require a large transformation ratio, and low voltage operation means high currents in the CMOS stage (sensitive to series resistance).
- 30 dBm of output power requires a matching ratio of 100 !

$$P_L = m \frac{V_{SW}^2}{2R_L} < m \frac{V_{DD}^2}{2R_L}$$

 $P_L < m \cdot \frac{1 \mathrm{V}^2}{2 \cdot 50 \Omega} = m \times 10 \mathrm{mW}$ 

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#### **LC Matching Network Loss**

 $\omega_0$ 

- The power loss of integrated matching networks is important.
- The insertion loss can be derived by making some simple approximations
- The final result implies that we should minimize our circuit Q factor and maximize the component Q<sub>c</sub>

$$P_{in} = P_L + P_{diss}$$

$$IL = \frac{P_L}{P_{in}} = \frac{P_L}{P_L + P_{diss}} = \frac{1}{1 + \frac{P_{diss}}{P_L}}$$

$$W_m = \frac{1}{4}Li_s^2 = \frac{1}{4}\frac{v_s^2}{4R_s^2}L$$

$$\times W_m = \frac{1}{4}\frac{v_s^2}{4R_s}\frac{\omega_0 L}{R_s} = \frac{1}{2}\frac{v_s^2}{8R_s}Q = \frac{1}{2}P_L \times Q$$

$$P_L = \frac{v_L^2}{2R_s} = \frac{v_s^2}{4 \cdot 2 \cdot R_s} = \frac{v_s^2}{8R_s}$$

$$\omega_0(W_m + W_e) = Q \times P_L$$

$$P_{diss} = \frac{P_L \cdot Q}{Q_c}$$

$$IL = \frac{1}{1 + Q}$$

 $1 + \frac{3}{6}$ 

#### **Multistage Matching**



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#### **Approximate Insertion Loss**

$P_{diss} = \frac{NQP_L}{Q_u}$			
	N	$Q~({\rm Eq.}~7.125)$	IL (dB) (Eq. 7.128)
$II = \frac{1}{1}$	1	9.95	-1.24
$IL = \frac{1}{1 + N\frac{Q}{Q}}$	2	3	-0.79
Qu	3	1.91	-0.76
	4	1.47	-0.78
$IL = \frac{1}{\sqrt{1}}$	5	1.23	-0.81
$1 + \frac{N}{Q_u} \sqrt{\left(\frac{R_{hi}}{R_{lo}}\right)^{1/N} - 1}$	6	1.07	-0.85

- Suppose a power amplifier delivering 100 W of power has an optimal load resistance of .5, but needs to drive a 50 IΩ antenna.
- Design a matching networkassuming that the component Q's of 30 are available.
- First note that a matching factor of m = 50/.5 = 100 is needed.
- Table above shows that 3 stages is optimum

#### **Technology Scaling**



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# **Technology Scaling**



source: Reynaert

#### **Quarter Wave Transformer**



$$P_L = \frac{|V^+|^2}{2Z_0} (1 - |\rho_L|^2) \qquad IL = \frac{P_L}{P_{in}} = \frac{1 - |\rho_L|^2}{e^{2\alpha\lambda/4} - |\rho(\lambda/4)|e^{-2\alpha\lambda/4}}$$

- Quarter wave line is a nice way to impedance match source and load. T-line comes for free since we can use the board trace at high frequency.
- How does this vary with matching ratio?

#### **T-Line Loss**



 For FR4 and other lossy dielectrics, the IL can be quite high. Multi-section T-line helps (lower Q) but area is a big constraint.

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#### **Transformer Matching**



$$IL = \frac{R_L}{r_1 + r_2 + R_L + \left(\frac{L_2}{M}\right)^2 r_1 + \frac{r_1(r_2 + R_L)^2}{\omega^2 M^2}}$$

 Key result: loss is nearly independent of the matching ratio!

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 $IL \approx \frac{R_L}{r_1 + r_2 + R_L + \frac{r_1}{N^2 Q_2^2}}$ 

# Simbürger PA Interstage Drive



- Simburger and co-authors demonstrated that on-chip transformer can be used to drive large bipolar PA devices
- Output power ~ 5W, 55% PAE

#### Simbürger Transformer



- Siemens team showed that on-chip transformers were useful for PA interstage matching.
- Can they be used for the output stage as well? ... Caltech DAT

# **Planar Transformer Layout**



- Moderately high k factor transformers can be realized using two metal layers
- Different layout styles offer an asymmetric primary/ secondary, a symmetric prim/sec, and a fully balanced and symmetric prim/sec

#### **Transformer Turns Ratio**



- With a planar layout, turns ratio can be obtained from omitting turns on the secondary or by connecting secondary turns in parallel
- Parallel connection offers lower loss on secondary

#### **High Turns 3D Ratio Transformers**



# **Balun Layout**



- Symmetric structures can be used to build baluns.
- Baluns are a natural fit in fully differential circuits.

#### **Lumped Modeling of Transformer**



- Symmetric 2π model
- RL network models frequencydependent loss
- Winding capacitance for SRF
- Asymmetric substrate network
# **Comparison of Results**



- Necessary to match both y, z parameters instead of sparameters only
- Good match up to high frequencies

#### **Transformer Resonant Modes**



- Two modes due to odd and even excitation.
- In "even" mode the coupling capacitor Cc is not excited.



# **Transformers Comparison**

- Paper published at RFIC 2004:
  - "Microwave Performance of Monolithic Silicon Passive Transformers", Mounir. Y. Bohsali and Ali. M. Niknejad
  - Compare various transformer layouts
  - Define metric that takes into account bandwidth

#### **Shunt versus Planar**



- Planar versus shunt have similar behavior below "resonance" with 2-3 dB of loss.
- Series structure has much lower resonance frequency.

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## **Transformer Bandwidth**



- Define a new metric: bandwidth over which gain is within 1 dB of "optimal" gain (for a bi-conj. match)
- Planar structure has very good bandwidth (50-150%), and other structures are worse, but series structure is significantly worse.
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# **Transmission Line Balun**



- Turn parasitic coupling capacitance into a distributed broadband transmission line!
- Excite the differential mode rather than the odd mode.



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#### **Broadband Inverter**



- The voltage at the load is inverted if the length of the line is small (~1/10 wavelength)
- Note that line excited with both odd and even mode at source but higher Z0 and loss of line rejects even mode.

# **LC Coupler**

- Lumped 180° coupler
- Low bandwidth (20%)
- Element values

$$\frac{1}{\omega C} = \omega L = \sqrt{2}Z_0$$



# **LC Balun**



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- Essentially a bridge with phase lead and lag networks.
- Bandwidth? Depends on Q of match since this is just a high-pass and low-pass matching network.

 $Z_c = \sqrt{R_i R_L}$ 

$$L = \frac{Z_c}{\omega} \quad C = \frac{1}{\omega Z_c}$$

# **Measured Lumped Balun**

20% fractional bandwidth
IL low due to substrate
Phase/amplitude balance relatively poor.





Frequency	5.8-6.8 GHz
Return Loss	11 dB
Insertion Loss	0.7 dB
Amplitude Imbalance	0.5 dB
Phase Imbalance	3.6°

#### An Integrated Double Balanced Mixer on Multilayer Liquid Crystalline Polymer (M-LCP) Based Substrate

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#### **Transmission Line Balun**



 This works as a balun over a very broad band. If length is quarter wavelength, the even mode is rejected at center frequency.

$$G_v = \frac{v_L}{v_s} = \frac{2}{\cos k\ell + j \sin k\ell \frac{Z_0}{2R_s}} = \frac{2}{e^{jk\ell}} = 2e^{-jk\ell}$$

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# **Marchand Balun**



- Improved bandwidth
- Less sensitivity to even-mode impedance
- Requires two quarter wave structures.

# **Wilkinson Power Combiner**



- Theoretically we cannot build a *lossless* 3 port device with isolation and power combining.
- The Wilkinson uses a resistor that is normally "open circuited" (even mode) and does not generate loss.
- Effective for high frequency designs or using LC circuit at low frequency.

# **Cal Tech DAT**



 Use virtual grounds wisely to turn 1:1 coupled lines into a transformer loop.

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## **Transformer FOM**

- Unlike inductor Q factor, there is no obvious "silver bullet"
   FOM for transformers.
- For power combining applications, the maximum power gain (bi-conjugate match) has been used as a figure of merit
- For a simple 1:1 transformer, the maximum gain is a function of only the *Q* and *K* factors

$$G_{max} = \frac{y_{21}}{y_{12}} (k - \sqrt{k^2 - 1}) = k - \sqrt{k^2 - 1}$$
$$Z = \begin{pmatrix} R_p + j\omega L_p & j\omega M \\ j\omega M & R_s + j\omega L_s \end{pmatrix}$$
$$k = \frac{2\Re(z_{22})\Re(z_{11}) - \Re(z_{21}z_{12})}{|z_{21}z_{12}|}$$
$$k = \frac{2R_x^2 + \omega^2 M^2}{\omega^2 M^2} = \frac{2R_x^2 + \omega^2 K^2 L^2}{\omega^2 K^2 L^2}$$
$$G_{max}(Q, K) = 1 + \frac{2}{Q^2 K^2} - 2\sqrt{\frac{1}{Q^4 K^4} + \frac{1}{Q^2 K^2}}$$

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# **Transformers for Power Combining**



- Notice that relatively low insertion loss is possible with moderate on-chip Q and K factors, thus allowing fully-integrated transformers
- Connecting 1:1 transformers in series and shunt, we can perform efficient power combining *independent* of the number of sections [Caltech DAT architecture]

#### **Transformer Power Combining Layout**



- Very simple layout
- Don't get DAT benefit → have extra "leads" that waste power
- But can turn off individual stages for power back-off
- Can easily scale power by adding more stages: design core driver stage

# **Fully Integrated Dual Mode CMOS PA**



Peak Output Power Mode

Power Back-off Mode

# **Power Combining and Control**



#### **Power Control and Efficiency Enhancement**



# **Load Modulation**

$$Z_{m,j} = \frac{\left(R_L + \sum_{i=1}^N m_i^2 \cdot R_{PA,i}\right) \cdot V_{pa,j}}{m_j \cdot \sum_{i=1}^N m_i \cdot V_{pa,i}} - R_{PA,j} \longrightarrow R_m = \frac{R_L}{N \cdot m^2}$$
$$P_o = N^2 \cdot m^2 \cdot \frac{V_p^2}{2R_L}$$

- In general there is no isolation in the transformer so the load current of one primary will "pull" the impedance of another primary.
- It's only under the special circumstance that all windings are driven in phase that we obtain isolation.

# **Efficiency at Back-Off**



- When all four stages are on, each PA see's  $\frac{1}{4}$  of the load.
- Suppose 2 stages are turned off. Then the PA's see ½ the load. The voltage swing at the output drops, but the voltage on each primary remains the same!
- For Class B operation, we can theoretically achieve the same efficiency at back-off.

#### **Power Back-Off Mode**

$$R = \frac{1}{3}R_L$$

$$A_{unit} = gm \cdot \frac{1}{3}R_L$$

$$V_o = A_{unit} \cdot V_i = gm \cdot \frac{1}{3}R_L \cdot \frac{3}{4}V_{i,\max} = V_{o,\max}$$

 $\eta_{overall} = \eta_{unit} = \eta_{max}$ 

$$A_{overall} = N \cdot A_{unit} = gm \cdot R_L$$

$$P_{out} = N \cdot P_{unit} = 3 \cdot \frac{1}{2} \frac{V_o^2}{\frac{1}{3}R_L} = \frac{9}{2} \frac{V_o^2}{R_L} = \frac{9}{16} P_{peak}$$

- Say we back-off the input by 3/4.
- If we turn off one amplifier, the load seen by each amplifier is now 1/3
- But the output voltage is still at the peak optimal value
- The overall efficiency is therefore at the peak value.

# A 1.2V, 2.4GHz Fully Integrated Linear CMOS PA with Efficiency Enhancement

# CICC 2006 Gang Liu<sup>1,2</sup>, Tsu-Jae King Liu<sup>2</sup> Ali M. Niknejad<sup>1,2</sup>

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# **Simplified 4-Way Combiner Schematic**



- Combing power from 4 unit amplifiers
- Centering at 2.4-GHz

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# **Schematic of Each Unit Amplifier**



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#### **Cascode Layout**



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# **Die Microphotograph**



# **Transformer & Cap Array**



#### **Single-Tone Test**



Freq = 2.4-GHz, Peak Power Mode

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#### **Two-Tones Test**



Freq = 2.4-GHz, 1-kHz tone spacing, Peak Power Mode

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# **Measured Efficiency at Back-Off**



Note: at 2.5-dB back-off, one unit amplifier was turned off.

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# **Measurements with EDGE Signals**



Freq = 2.4-GHz, Peak Power Mode

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#### **Measurements with 802.11g Signals**



 $P_{out} = 14.5 - dBm$  EVM = 4.48%

Freq = 2.4-GHz, Peak Power Mode

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#### **EVM vs Output Power**



#### **Table of Performance**

Technology	0.13-µm RF CMOS
Supply voltage	1.2-V
DC Current	114-mA
P <sub>-1dB</sub>	24-dBm
Drain efficiency	25%
Saturated Power	27-dBm
Drain efficiency	<b>32%</b>
# A 5.8 GHz Linear Power Amplifier in a Standard 90nm CMOS Process using a 1V Power Supply

#### RFIC 2007

Peter Haldi, Debopriyo Chowdhury, Gang Liu and

Ali M. Niknejad

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## **New Transformer Network**



- Figure "8" style layout minimized the impact of lead inductance
- Lateral coupling used since top metal layer is most conductive and most distant from substrate
- Very good isolation characteristic due to flux inversion

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## Improved Layout...



- Using two primary windings
  - Improved coupling
  - Lower loss (current crowding at edge of conductors)
  - More symmetric primary/secondary for optimal power transfer

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## **Prototype PA in Digital CMOS**



- Four stage differential design
- Single-ended
  50Ω output
- Thin oxide
  90nm
  transistors

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### **Measured Output Power**



 Peak power is 24 dBm. Good match to simulation up to 1dB compression point.

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#### **Measured Efficiency**



# **PA Linearity**



- IM3 = 28 dBc at output power of 20.5 dBm (200 MHz)
- IM3 has tone spacing dependence due to lack of good bypass (class AB stage). Verified with packaged version. UC Berkeley, EECS 242

#### **Output Power vs Frequency**



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# **CMOS "digital" Prototype**

			· /					
Process	Freq.	$V_{dd}$	$P_{1dB}$	IM3	Gain	$\eta$	Ref.	Notes
$0.35 \mu m$ RF	1.91 GHz	2.5V	23.5dBm		24.6  dB	35.3%	[19]	with driver, ext. RF
CMOS								chokes
$0.5\mu m$ SiGe BiC-	$1.75~\mathrm{GHz}$	3.3V	24dBm	$37 \mathrm{~dBc}$	$23.9\mathrm{dB}$	29.2%	[20]	with driver, linearized
MOS								
$0.18 \mu m$ standard	$2.4~\mathrm{GHz}$	3.3V	24.5dBm		$19.8~\mathrm{dB}$	31\3%	[9]	with driver
CMOS								
$0.13 \mu m$ RF	$2.4~\mathrm{GHz}$	1.2V	24dBm	29dBc	10  dB	25%	[8]	
CMOS								
$0.09 \mu m$ standard	5.2-5.8 GHz	1V	23.3dBm	$30.5 \mathrm{dBc}$	$13.8~\mathrm{dB}$	26%	this work	simulated results
CMOS								

Table 5.3: Comparison between state of the art linear power amplifiers.

- New transformer layout has simulated efficiency of 75%
- State-of-the-art performance of 5 GHz linear PA
  - 24 dBm with 27% efficiency

# **4G Wireless Communication**



- IEEE 802.16 standard (Wireless MAN)
- Wireless data over long distances in a variety of ways

### **Two-Stage WiMAX CMOS PA**



# **Output Stage Design**



- Thick-oxide CG stage ( $V_{DD} = 3.3V$ )
- Dynamic gate biasing
- Capacitive divider
- Differential → does not affect small signal gain

#### **Large-Signal CW Measurements**



# **Meeting the WiMAX Mask**



• Average Pout = 22.76 dBm

- Average drain efficiency = 15%, Average PAE = 12%
- Power of 2nd, 3rd and higher harmonics also meet FCC mask → possible to eliminate harmonic filter

### **Back-Off Mode Implementation**



- Bottom stage powered-down for low-power mode
- Vctrl=0 in high-power mode and 2\*V<sub>DD</sub> in low-power mode

#### **Low Power Mode**



## **Common-Mode Stability**



- Pseudo-differential architecture → common-mode oscillations possible
- Need to consider ground & supply inductances, bypass network

### **A Simpler Structure**



• If  $(1/\omega C_{gd}) >> (\omega^* L)$ ,

$$Z_{IN} = \frac{1}{\left(1 + \omega g_m L_D\right)^2} \left[\frac{1}{j\omega C_{gd}} - \frac{g_m L_D}{C_{gd}}\right]$$

**Ref: [Cripps]** 

# **Stability Analysis**



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# **Stabilizing the PA**

- Resistor in series with gate
- Resistor in series with bypass capacitor
- Staggered-RC bypass network
- Series RC-pair



 $\mathsf{V}_{\mathsf{DD}}$ 

## **Series RC Pair**

